INFORMATION DISCLOSURE CITATION PTO-1449			Customer Number: 26615		ATTORNEY'S DKT No. H1174 APPLICANT(S) Chih-Yuh Yang et al.		APPLICATION NO. Unassigned		
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fo	Digh Hisamoto IEEE Transaction 2325.	et al., "F ns on Ele	inFET-A Self- ectron Device	Aligned s, Vol. 4	Double-Gate I 17, No. 12, De	MOSFET :	Scalable to 2 2000, pages	2320-	
).	Yang-Kyu Choi et al., "Sub-20nm CMOS FinFET Technologies," 2001 IEEE, IEDM, pages 421-424.								
	Xuejue Huang et al., "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pages 880-886.								
	Xuejue Huang et al., "Sub 50-nm FinFET: PMOS," 1999 IEEE, IEDM, pages 87-70.  Yang-Kyu Choi et al., "Nanoscale CMOS Spacer FinFET for the Terabit Era," IEEE Electron								
1	Device Letters,	Vol. 23,	No. 1, Janua	ry 2002	, pages 25-21	7.			
TOPA	Co-pending U.S. Application Serial Number 10/348,758 filed January 23, 2003 entitled, "GERMANIUM MOSFET DEVICES AND METHODS FOR MAKING SAME," Judy Xilin An et al., 22 page specification, 29 sheets of drawings.								
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